



# A Cantilever-based Non-volatile Memory Utilizing Vibrational Reset for High Temperature Operation

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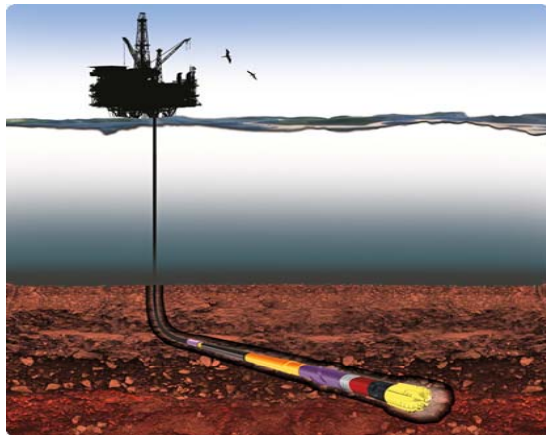
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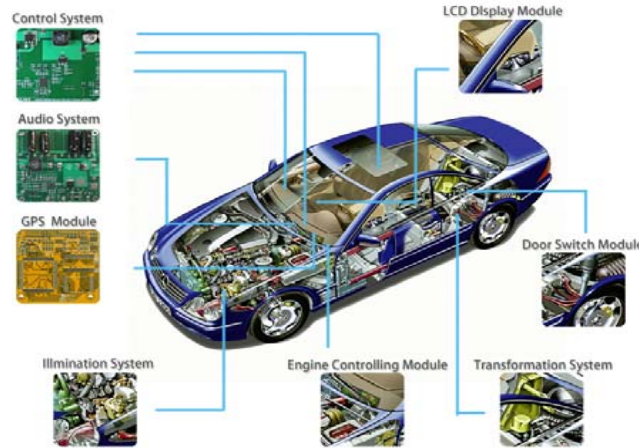


# Introduction

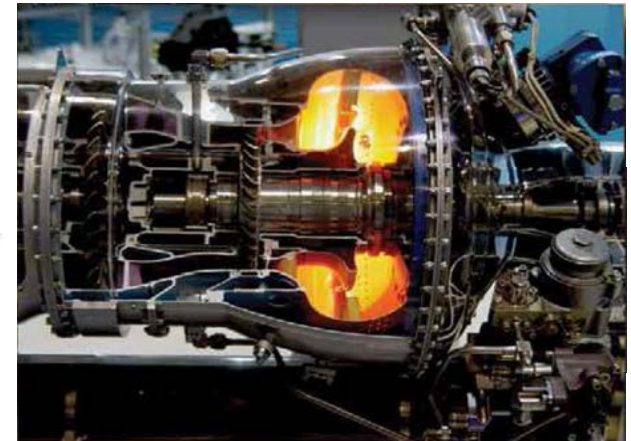
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Oil Rig Industry

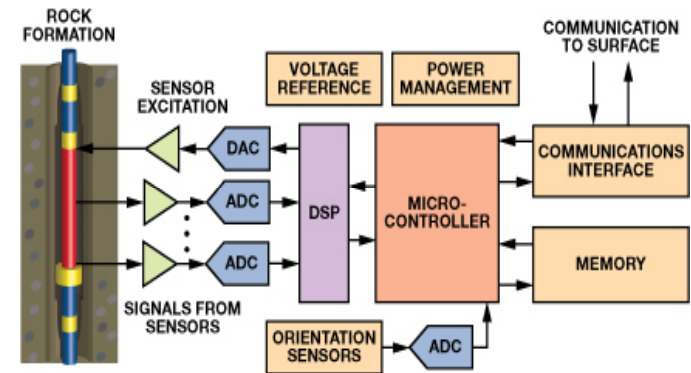


Automotive

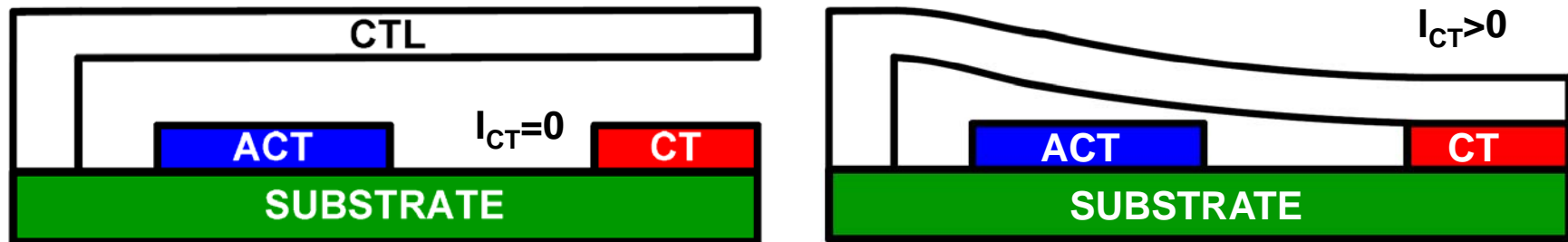


Aviation

- Memory device for data logging in harsh environment are highly demanded
- Market Available flash memory exhibits poor retention when exposed to high temperature(  $> 200^{\circ}\text{C}$ )



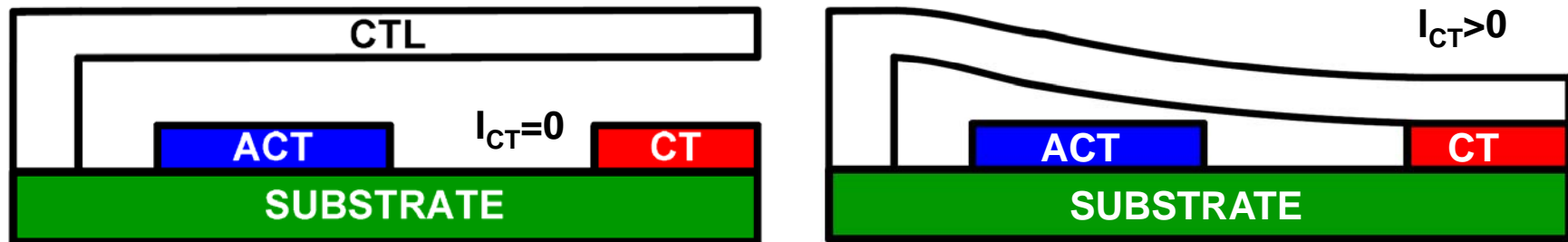
# Anchored NEMS Memory Device



ACT: Actuator, CT: Contact, CTL: Cantilever

- The proposed device has three terminals (**CTL: Cantilever, ACT: Actuator, CT: Contact**).
- Cantilever is actuated by Actuator with bias voltage.
- Actuation is performed by **electrostatic force** between Actuator and Cantilever .

# Anchored NEMS Memory Device

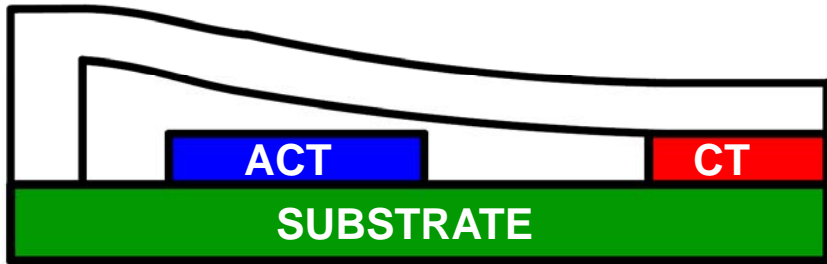


ACT: Actuator, CT: Contact, CTL: Cantilever

- Data retention is realized by **Van der Waals** force.
- No memory operation is obtained when **Van der Waals** force is small.
- Data read-out is carried out by sensing the current between Cantilever and Contact terminals.

# Data Retention Principle

- Magnitude  $F_{ad}$  of the adhesive (Van Der Waals) force :

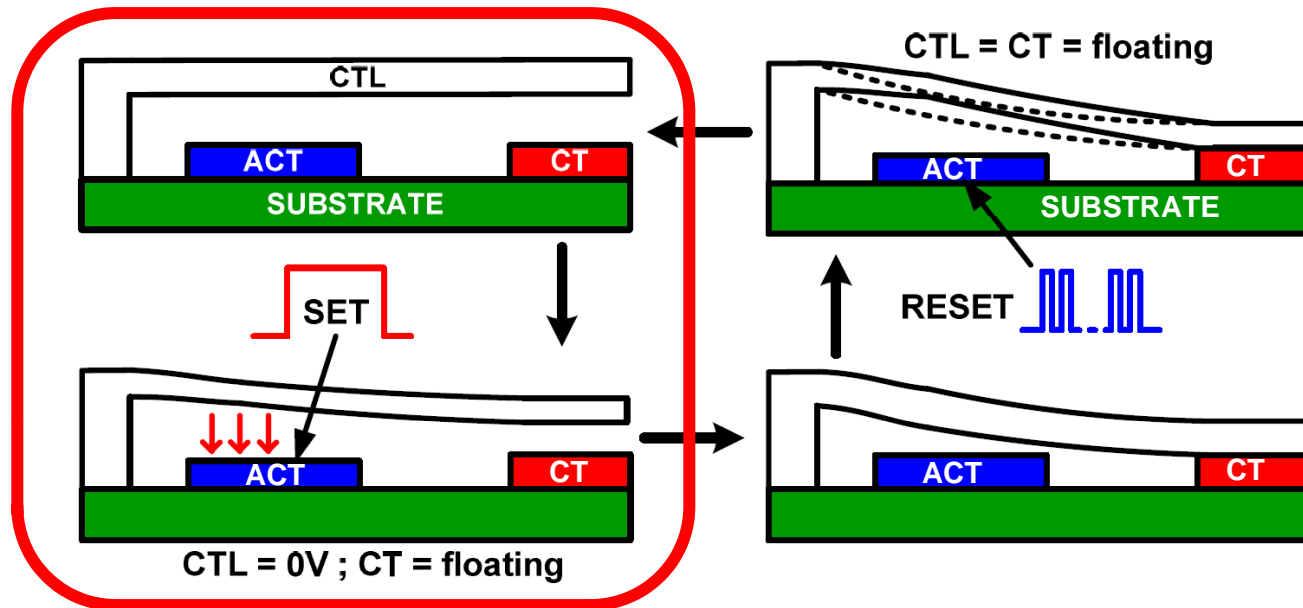


The diagram illustrates a cross-section of a magnetic head assembly. A green substrate is at the bottom. On top of it, there is a blue rectangular block labeled 'ACT' and a red rectangular block labeled 'CT'. A thin, curved metal layer is positioned above these blocks, with its ends connected to a larger structure above. A red arrow points from the metal layer towards the equation on the right.

$$F_{ad} = \frac{A_{metal}}{12 \cdot \pi \cdot D_{rms}^2}$$

- $A_{metal}$  : Hamaker constant of the metal,  $D_{rms}$  : Surface roughness
- $F_{ad}$  increases with temperature, thus data retention improves at higher temperature.

# Actuation Principle



ACT: Actuator, CT: Contact, CTL: Cantilever

- **SET pulse** is applied to Actuator (CTL = GND) to create electrostatic force.
- Cantilever is pulled down and remains **in contact** by **Van der Waals** force.

# Actuation Principle

- $F_r$  - magnitude of **restoring force**,  $F_{ad}$  - magnitude of **adhesion force**

$$F_r = \frac{EWt^3g}{4L^3}$$

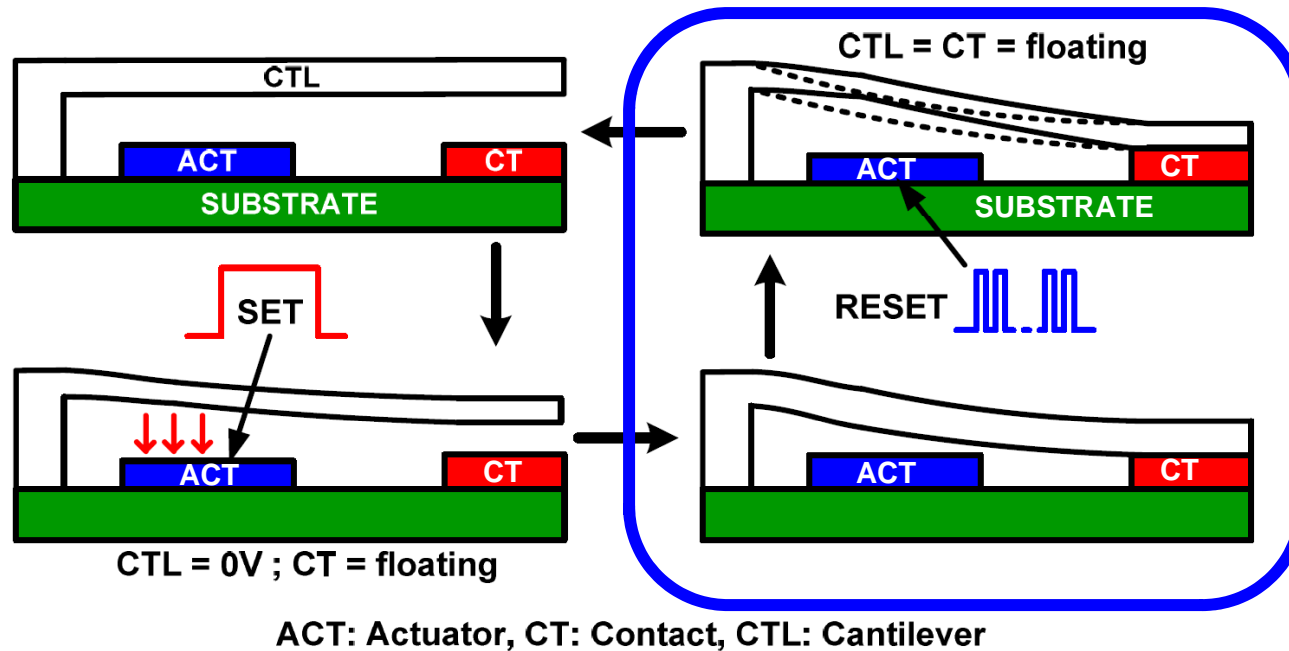
$$F_{ad} = \frac{A_{metal}}{12\pi D_{rms}^2}$$

- For adhesion:  $F_{ad} > F_r$
- The adhesion force can be made larger by carefully engineering the **smoothness**, the size of the Contact and Cantilever and **number of dimples**



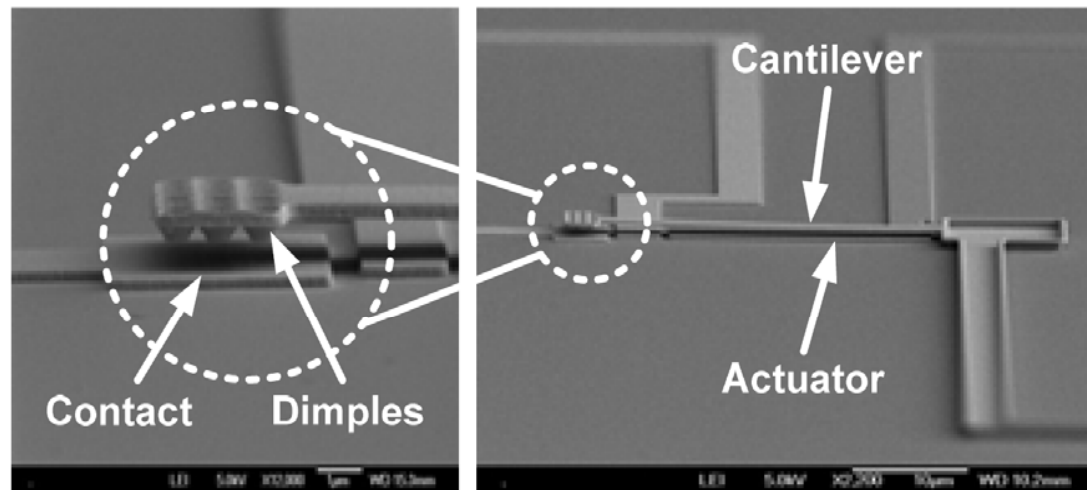


# De-actuation Principle



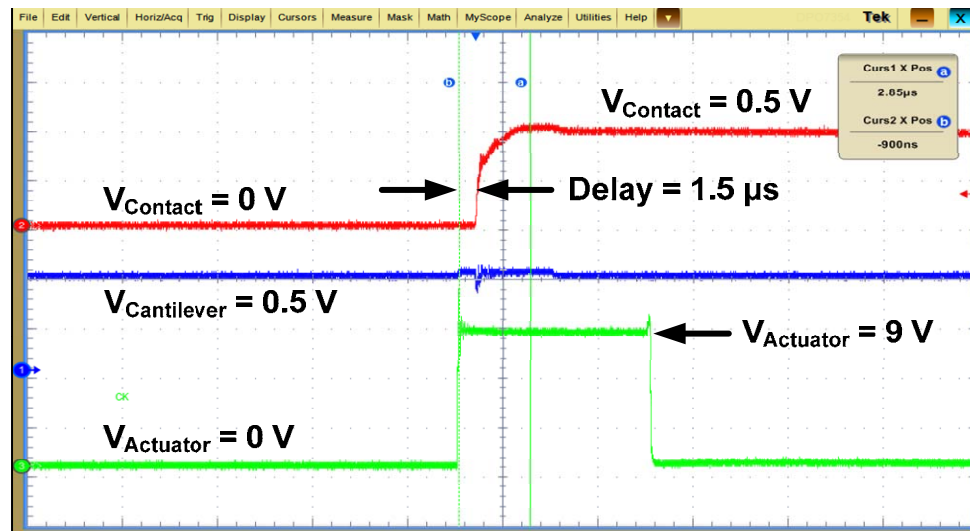
- **RESET** is carried out by applying a **train of short pulses** to the actuator.
- Cantilever starts vibrate if the pulse frequency matches the **resonant frequency** of Cantilever.

# Fabricated Device



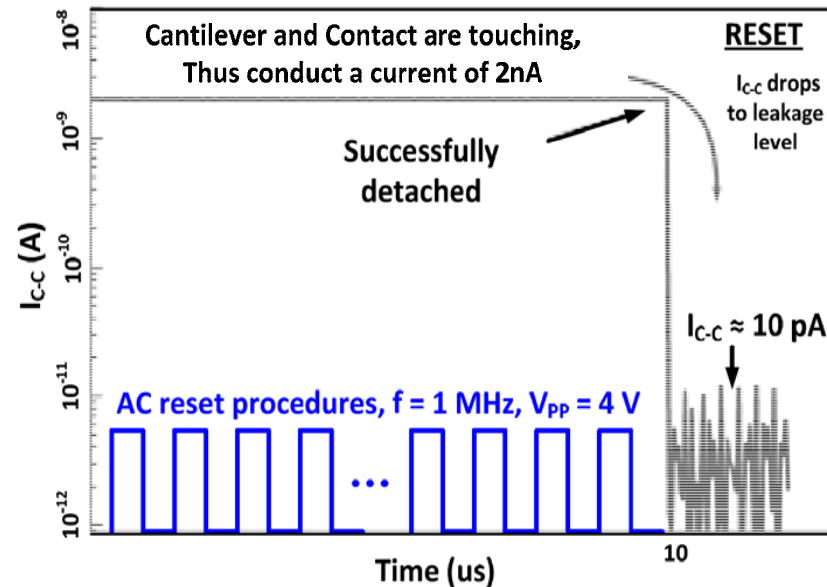
- The head of the Cantilever beam has array of **dimples**. (500 nm × 500 nm).
- The number of dimples is of crucial as it decides the adhesion force between Cantilever and Contact.

# Measurement Results-Set



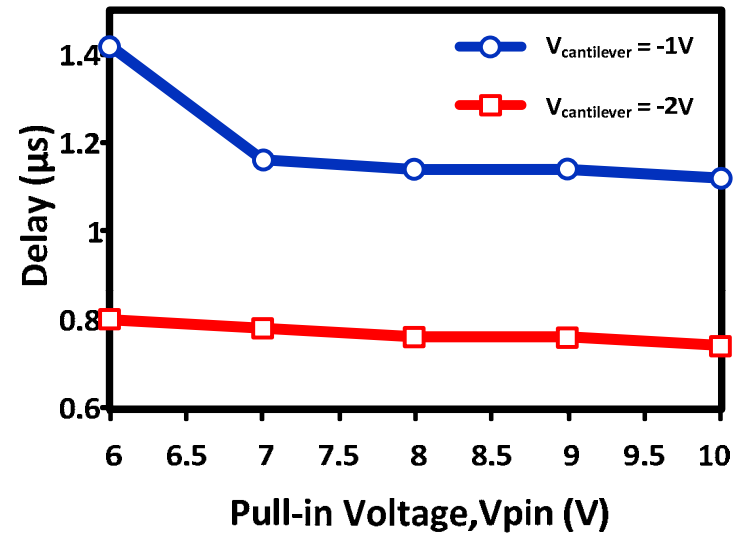
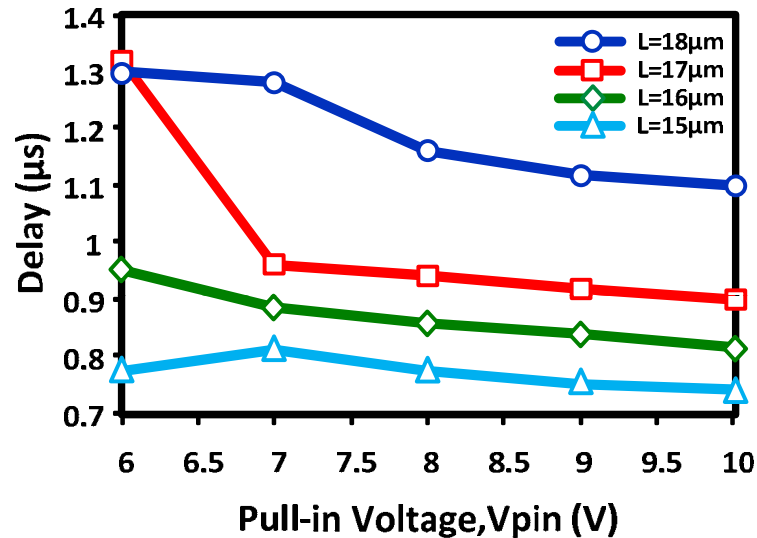
- A long single pulse is applied for SET.
- The contact follows the cantilever voltage (0.5V) when SET is achieved.
- Read delay of 1.5  $\mu\text{s}$  was measured at 9V.

# Measurement Results-Reset



- A train of short pulses is applied for RESET.
- The measured Cantilever-Contact current falls to  $10\text{ pA}$  when RESET is achieved. (Max. current is limited by external equipment for device protection.)

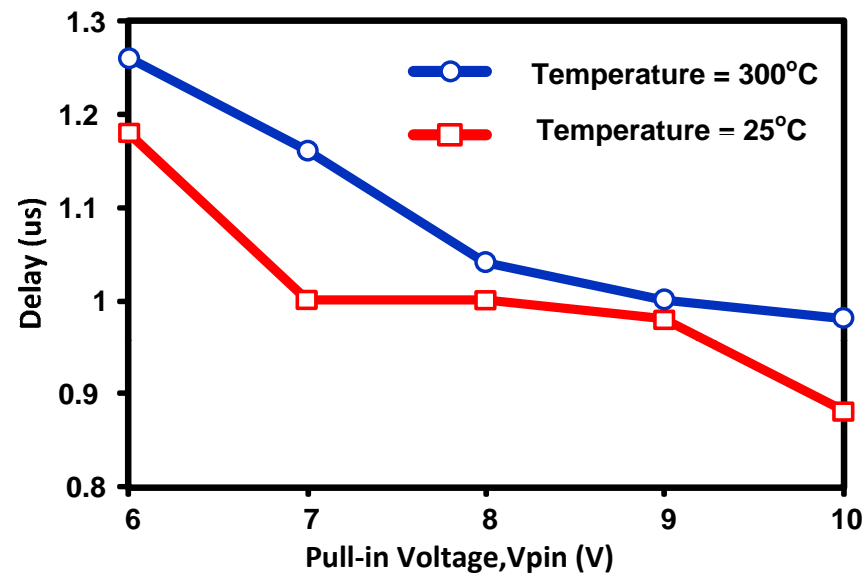
# Performance Evaluation – “SET”



- Delay can be reduced by decreasing Cantilever length and increasing pull-in voltage.
- Delay decreases by lowering Cantilever voltage below GND.

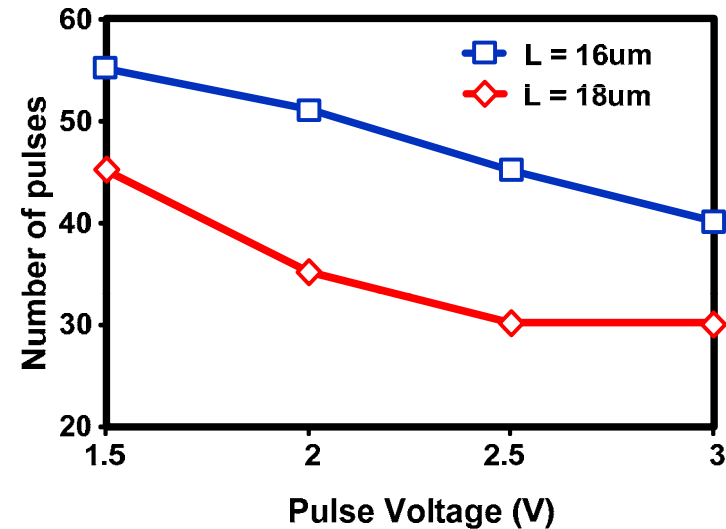
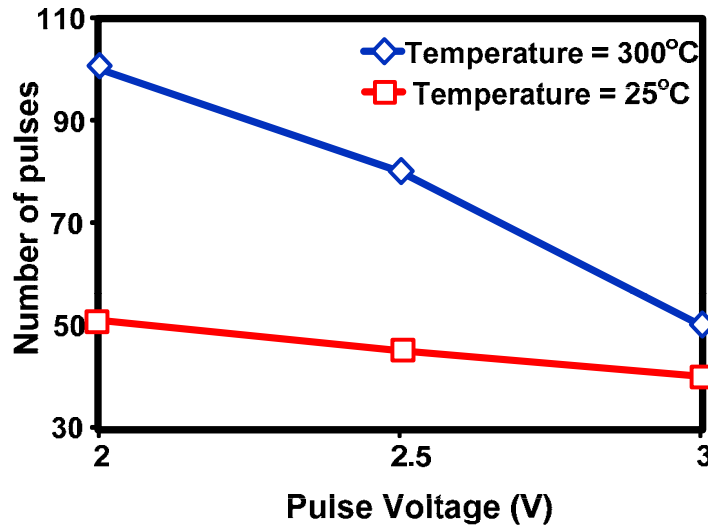


# Performance Evaluation – “SET”



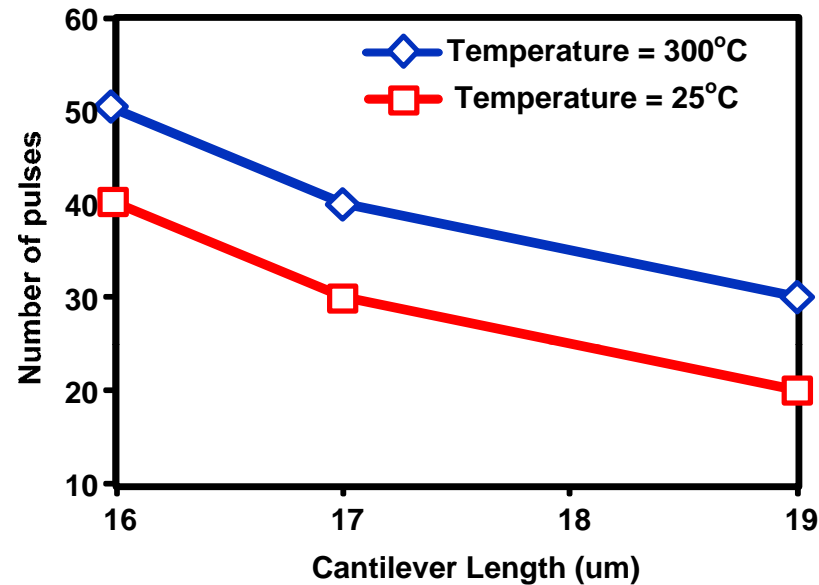
- The variation in delay w.r.t pull-in voltage is less when the temperature increases.
- The trend is same for both low and high temperature. (shows working of device at high temperature)

# Performance Evaluation – “RESET”



- Number of pulses required for de-actuation reduces as the pulse voltage increases.
- As the length increases the number of pulse reduces due to less stiffness.

# Performance Evaluation – “RESET”

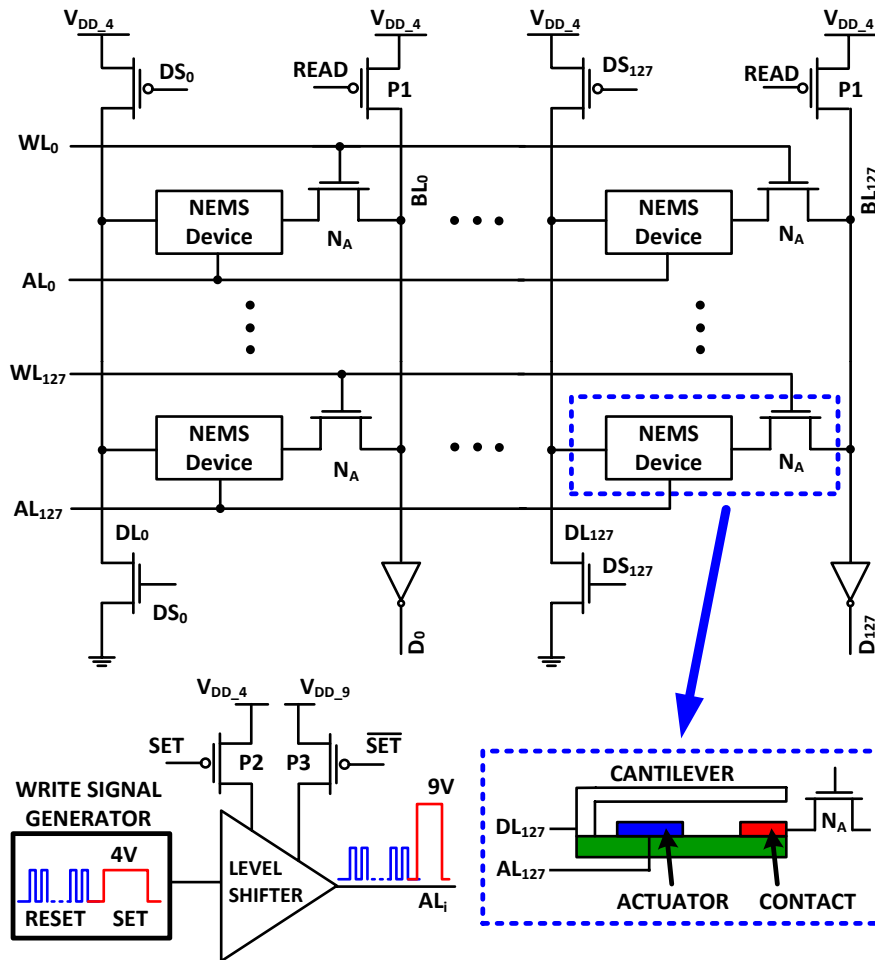


- The number of pulses required increases with temperature, due to increase in adhesion force.
- At high temperature, increase in cantilever length decreases number of pulses as at low temperature.



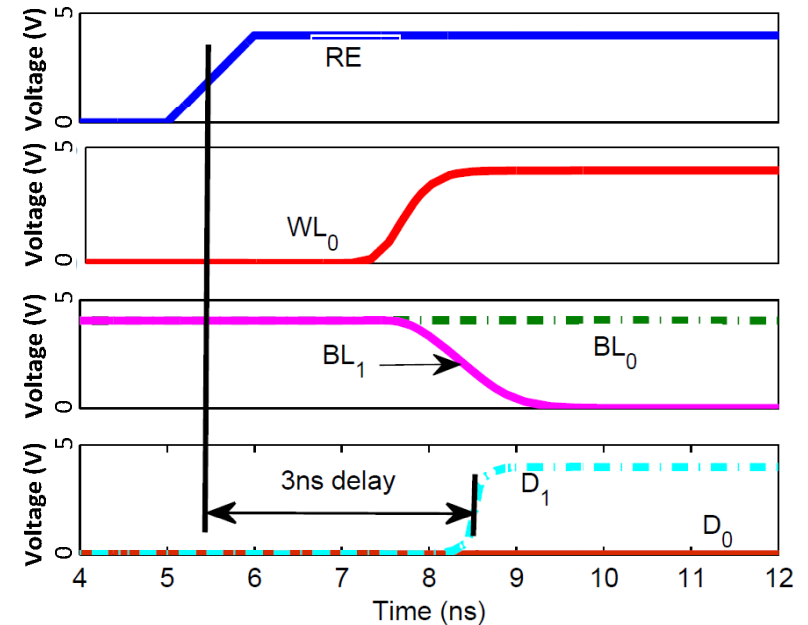
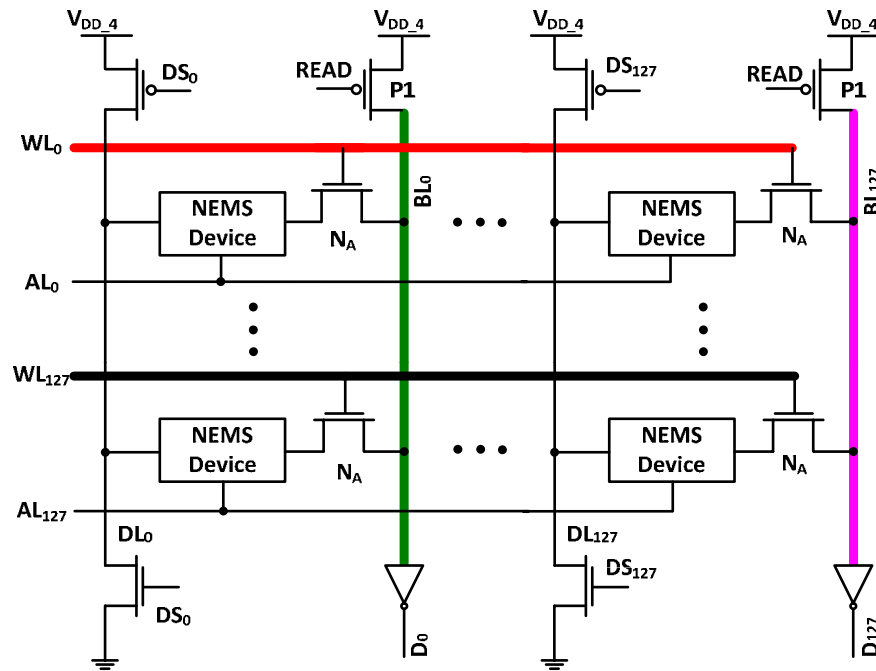


# Proposed array organization



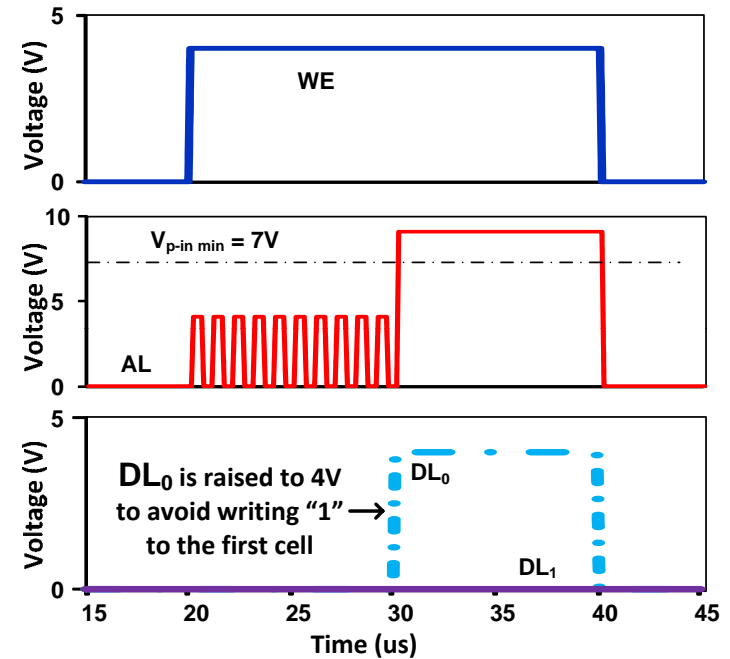
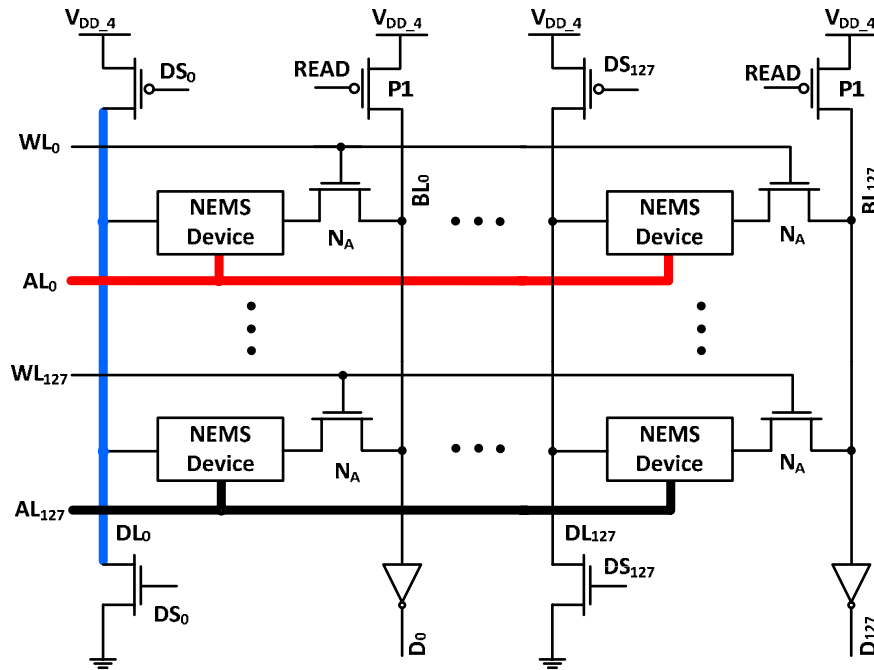
- Array structure has:
  - **1NEMS-1T** memory cell
  - Two horizontal lines ( $WL_i$  and  $AL_i$ ) per row, two vertical lines ( $DL_i$  and  $BL_i$ )
  - $DL_i$  is connected to Cantilever
  - $AL_i$  is connected to Actuator
  - Contact is connected to access device ( $N_A$ )

# Proposed Read Operation



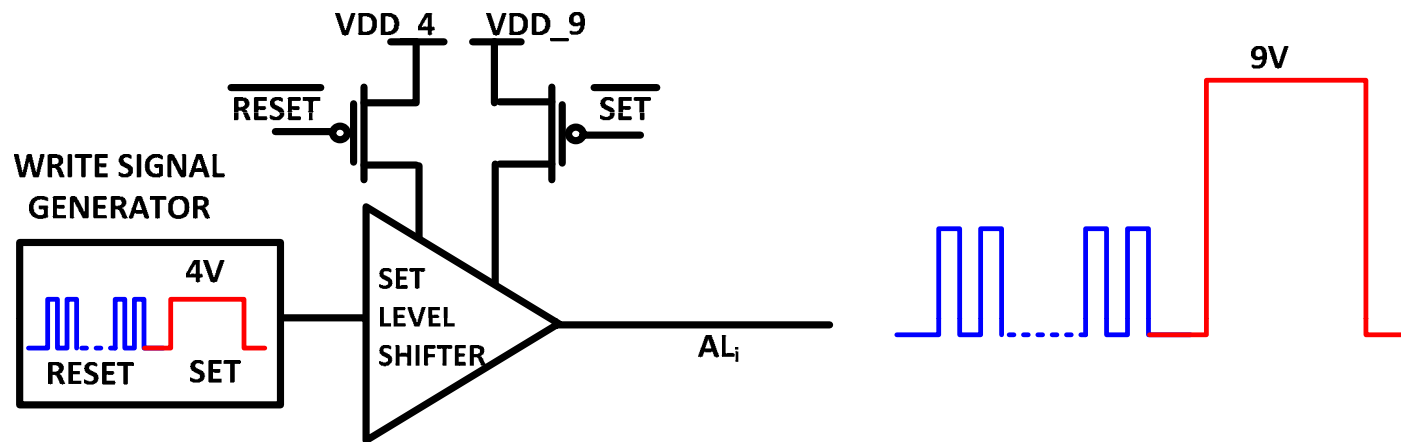
- **BLs are pre-charged to  $V_{DD}$  by PMOS (P1) devices.**
- **If Cantilever is at contact (i.e. Data = "1"), BL follows DL through access devices ( $N_A$ ).**

# Proposed Write Operation



- Write data pattern is “01011....1”.
- $DL_0$  is raised to 4V to avoid writing “1” to the first cell as the datum to first cell is “0”.

# Proposed Write Operation



- Write “1” or “0” can be done by flipping the stored data.
- **RESET** is performed before every write operation.
- A Level Shifter is used to supply the  $V_{p-min}$  for the actuation of cantilever.

# Conclusion

- A novel **NEM memory** device is proposed using Van-der-Waals force.
- A **memory array structure** is proposed.
- We propose a read/write scheme:
  - 1 NEMS–1 T bit cell
  - **Vibrational RESET** which eliminates the need for another terminal
  - Variation tolerance with temperature is addressed

